# Low Frequency Transistor (-32V, -0.8A)

# 2SB1197K

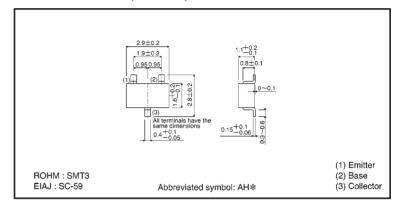
# Features

1) Low VCE(sat).  $V_{CE(sat)} \leqq -0.5V \\ (I_c / I_B = -0.5A \ / \ -50mA)$ 

- 2)  $I_c = -0.8A$ .
- 3) Complements the 2SD1781K.
- Structure

Epitaxial planar type PNP silicon transistor

# External dimensions (Units: mm)



# ●Absolute maximum ratings (Ta = 25°C) \* Denotes her

Parameter	Symbol	Limits	Unit
Collector-base voltage	Vсво	-40	V
Collector-emitter voltage	VCEO	-32	V
Emitter-base voltage	VEBO	-5	V
Collector current	Ic	-0.8	А
Collector power dissipation	Pc	0.2	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55~+150	°C

## • Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВУсво	-40	_	_	٧	Ic=-50 μ A
Collector-emitter breakdown voltage	BVCEO	-32	_	_	٧	Ic=-1mA
Emitter-base breakdown voltage	ВУЕВО	-5	_	_	٧	I <sub>E</sub> =−50 μ A
Collector cutoff current	Ісво	_	_	-0.5	μΑ	V <sub>CB</sub> =-20V
Emitter cutoff current	<b>I</b> EBO	_	_	-0.5	μΑ	V <sub>EB</sub> =-4V
Collector-emitter saturation voltage	V <sub>CE</sub> (sat)	_	_	-0.5	٧	Ic/I <sub>B</sub> =-0.5A/-50mA
DC current transfer ratio	hfE	120	_	390	_	V <sub>CE</sub> =-3V, I <sub>C</sub> =-100mA
Transition frequency	f⊤	50	200	_	MHz	V <sub>CE</sub> =-5V, I <sub>E</sub> =50mA, f=100MHz
Output capacitance	Cob	_	12	30	pF	V <sub>CB</sub> =-10V, I <sub>E</sub> =0A, f=1MHz

(96-134-B92)



**Transistors** 2SB1197K

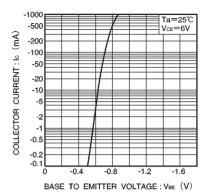
# Packaging specifications and here

		Package	Taping
		Code	T146
Туре	hfe	Basic ordering unit (pieces)	3000
2SB1197K	QR		0

hee values are classified as follows:

Item	Q	R
hfe	120~270	180~390

### Electrical characteristic curves



Grounded emitter propagation characteristics

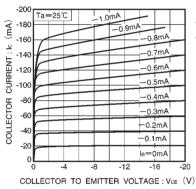


Fig.2 Grounded emitter output characteristics (I)

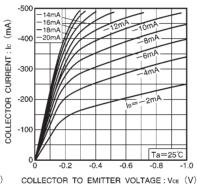


Fig.3 Grounded emitter output characteristics (II)

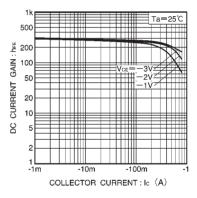


Fig.4 DC current gain vs. collector current

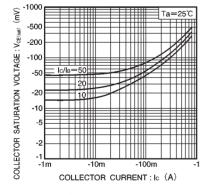


Fig.5 Collector-emitter saturation voltage vs. collector current

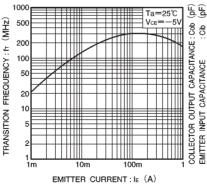
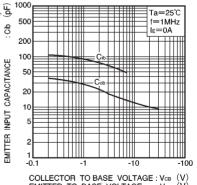


Fig.6 Gain bandwidth product vs. emitter current



COLLECTOR TO BASE VOLTAGE: VCB EMITTER TO BASE VOLTAGE: VEB

Collector output capacitance vs. collector-base voltage Emitter input capacitance vs. emitter-base voltage

Fig.7